Listing of Claims:

This listing of claims reflects all claim amendments and replaces all prior versions, and listings, of claims in the application. Material to be inserted is in **bold and underline**, and material to be deleted is in ~~strikeout~~ or (if the deletion is of five or fewer consecutive characters or would be difficult to see) in double brackets [[ ]].

1. (Previously Presented) A method of texturing a glass surface, the method comprising the steps of:

- coating the glass surface with an aluminium film,

- stimulating a reaction between the glass and the aluminium film resulting in the formation of reaction products at an interface between the glass and the aluminium film such that an interfacial surface of unreacted glass at the interface is textured, and

- removing the aluminium film and the reaction products from the glass surface by chemical etching.

2. (Original) The method as claimed in claim 1, wherein the step of stimulating the reaction at the interface comprises a thermal annealing process.

3. (Original) The method as claimed in claim 2, wherein the thermal annealing process comprises a sequence of annealing steps at different temperatures.

4. (Previously Presented) The method as claimed in claim 2, wherein the thermal annealing process is conducted in a controlled ambient atmosphere.

5. (Canceled)

6. (Previously Presented) The method as claimed claim 1, wherein the glass surface is initially substantially flat.

7. (Canceled)

8. (Previously Presented) The method as claimed in claim 1, wherein the reaction products comprise aluminium oxide and/or silicon.

9. (Previously Presented) The method as claimed in claim 1, wherein the step of removing the aluminium film and the reaction products comprises one or more etching steps.

10. (Canceled)

11. (Previously Presented) The method as claimed in claim 1, wherein the glass comprises quartz, float glass, or non-float glass.

12. (Previously Presented) A method of manufacturing a photovoltaic device, the method comprises the steps of texturing a glass surface utilizing a method as claimed in claim 1, and depositing a semiconductor film on the textured glass surface, whereby the glass-facing surface of the semiconductor film exhibits substantially the same degree of texture as the glass surface.

13. (Original) The method as claimed in claim 12, wherein the semiconductor film is deposited in a manner such that substantially no gaps or voids exist between the textured glass surface and the semiconductor film.

14. (Previously Presented) The method as claimed in claim 12, wherein the method further comprises forming a dielectric barrier layer between the glass and the semiconductor.

15. (Original) The method as claimed in claim 14, wherein the dielectric layer is formed on the textured glass surface prior to the deposition of the semiconductor film.

16. (Previously Presented) The method as claimed in claim 14, wherein the barrier layer comprises silicon oxide or silicon nitride.

17. (Previously Presented) The method as claimed in claim 12, wherein the semiconductor film comprises a crystalline and/or an amorphous semiconductor material.

18. (Original) The method as claimed in claim 17, wherein the semiconductor material comprises silicon.

19. (Previously Presented) A textured glass surface formed utilizing a method as claimed in claim 1.

20. (Previously Presented) A photovoltaic device manufactured utilizing a method as claimed in claim 12.

21.–25. (Canceled)